

TOSHIBA GTR MODULE SILICON N CHANNEL IGBT

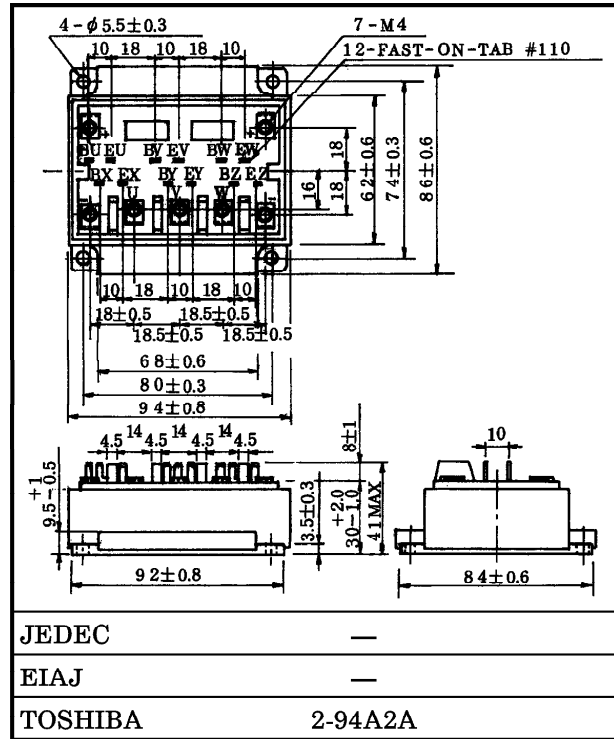
MG100J6ES50

HIGH POWER SWITCHING APPLICATIONS.

Unit in mm

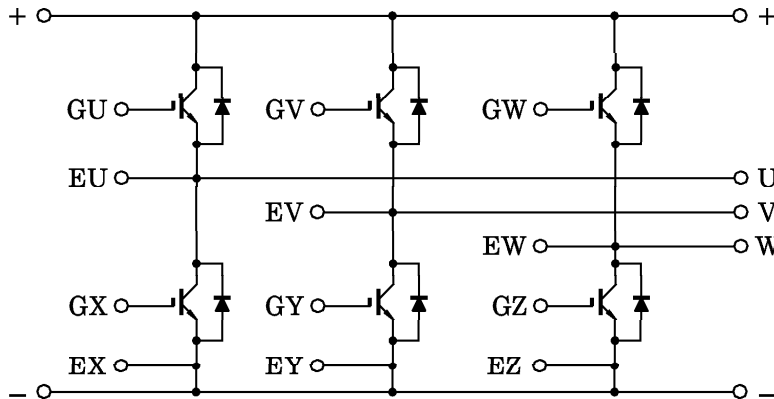
MOTOR CONTROL APPLICATIONS.

- The Electrodes are Isolated from Case.
- High Input Impedance.
- 6 IGBTs Built Into 1 Package.
- Enhancement-Mode.
- High Speed : $t_f=0.30\mu s$ (Max.) ($I_C=100A$)
 $t_{rr}=0.15\mu s$ (Max.) ($I_F=100A$)
- Low Saturation Voltage
: $V_{CE(sat)}=2.70V$ (Max.) ($I_C=100A$)



Weight : 505g (TYP.)

EQUIVALENT CIRCUIT



961001EAA2

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MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | RATING | UNIT |
|---|-----|-------------------|------------------|------|
| Collector-Emitter Voltage | | V _{CES} | 600 | V |
| Gate-Emitter Voltage | | V _{GES} | ±20 | V |
| Collector Current | DC | I _C | 100 | A |
| | 1ms | I _{CP} | 200 | |
| Forward Current | DC | I _F | 100 | A |
| | 1ms | I _{FM} | 200 | |
| Collector Power Dissipation (T _c = 25°C) | | P _C | 450 | W |
| Junction Temperature | | T _j | 150 | °C |
| Storage Temperature Range | | T _{stg} | -40~125 | °C |
| Isolation Voltage | | V _{Isol} | 2500 (AC 1 min.) | V |
| Screw Torque (Terminal/Mounting) | | — | 2/3 | N·m |

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|---------------------|----------------------|---|------|------|------|--------|
| Gate Leakage Current | | I _{GES} | V _{GE} = ±20V, V _{CE} = 0 | — | — | ±500 | nA |
| Collector Cut-off Current | | I _{CES} | V _{CE} = 600V, V _{GE} = 0 | — | — | 1.0 | mA |
| Gate-Emitter Cut-off Voltage | | V _{GE(off)} | I _C = 10mA, V _{CE} = 5V | 5.0 | 7.0 | 8.0 | V |
| Collector-Emitter Saturation Voltage | | V _{CE(sat)} | I _C = 100A, V _{GE} = 15V | — | 2.10 | 2.70 | V |
| Input Capacitance | | C _{ies} | V _{CE} = 10V, V _{GE} = 0, f = 1MHz | — | 9000 | — | pF |
| Switching Time | Turn-on Delay Time | t _{d(on)} | Inductive Load V _{CC} = 300V I _C = 100A V _{GE} = ±15V R _G = 13Ω (Note 1) | — | 0.08 | 0.16 | μs |
| | Rise Time | t _r | | — | 0.12 | 0.24 | |
| | Turn-on Time | t _{on} | | — | 0.40 | 0.80 | |
| | Turn-off Delay Time | t _{d(off)} | | — | 0.20 | 0.40 | |
| | Fall Time | t _f | | — | 0.15 | 0.30 | |
| | Turn-off Time | t _{off} | | — | 0.50 | 1.00 | |
| Forward Voltage | | V _F | I _F = 100A, V _{GE} = 0 | — | 2.30 | 3.00 | V |
| Reverse Recovery Time | | t _{rr} | I _F = 100A, V _{GE} = -10V di / dt = 100A / μs | — | 0.08 | 0.15 | μs |
| Thermal Resistance | | R _{th(j-c)} | Transistor | — | — | 0.28 | °C / W |
| | | | Diode | — | — | 0.69 | |

Note 1 Switching Time Test Circuit & Timing Chart

